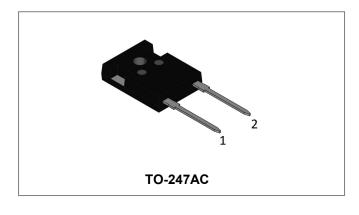






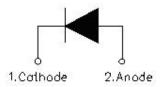
SDUR60H120W ULTRAFAST RECTIFIER



Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings@TA=25°C unless otherwise specified

Characteristics	Symbol	Condition Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	1200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=103°C, rectangular wave form	60	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	500	Α

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	O* V _{F1} @ 60A, Pulse,		2.70	3.20	٧
	V_{F2}	@ 60A, Pulse, T _J = 125°C	2.20	2.50	٧
Reverse Current*	I _{R1}	@V _R = rated V _R ,T _J =25°C	0.40	10	uA
	I _{R2}	@V _R = rated V _R , T _J =125°C	0.14	4	mA
Reverse Recovery Time	trr	I_F =500mA, I_R =1A,and I_m =250mA, T_J =25°C	61	75	ns
Reverse Recovery Time	t _{rr}	1 11 15/14 501/ 1/ 001/	52	-	ns
Reverse Recovery Charge	Qrr	$I_F = 1A$, diF/dt = 50A/ μ s, $V_R = 30V$, $I_{\perp} = 25$ °C	44	-	nC
Reverse Recovery Current	I _{RRM}	1.5 20 0	1.7	-	Α
Reverse Recovery Time	t _{rr}	1 004 PF/H 0004/	188	-	ns
Reverse Recovery Charge	Qrr	l I _F = 30A, diF/dt = 200A/μs, V _R = 600V. T ₋ ι = 25°C	489	-	nC
Reverse Recovery Current	I _{RRM}	VK 000V, 1,7 20 0	5.2	-	Α
Reverse Recovery Time	t _{rr}	1 20A JIF/JA 200A/	288	-	ns
Reverse Recovery Charge	Qrr	l _F = 30A, diF/dt = 200A/μs, V _R = 600V. T _J = 125°C	1786	-	nC
Reverse Recovery Current	I _{RRM}	11. 3331, 13 120 0	12.4	-	Α

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

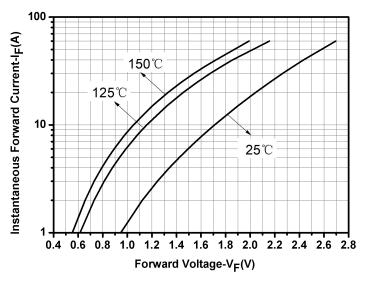
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.80	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AC			







Ratings and Characteristics Curves



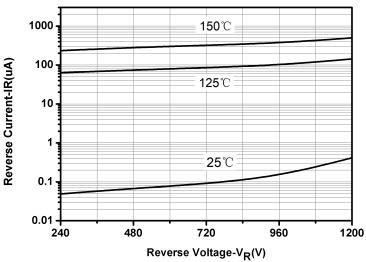
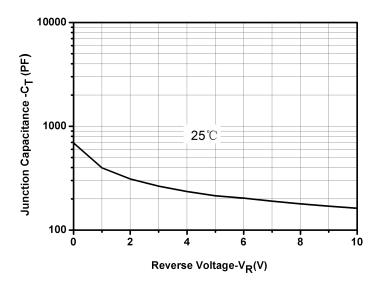


Fig.1-Typical Forward Voltage Characteristics

Fig.2-Typical Reverse Characteristics



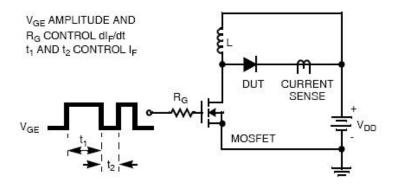


Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Diode Test Circuit

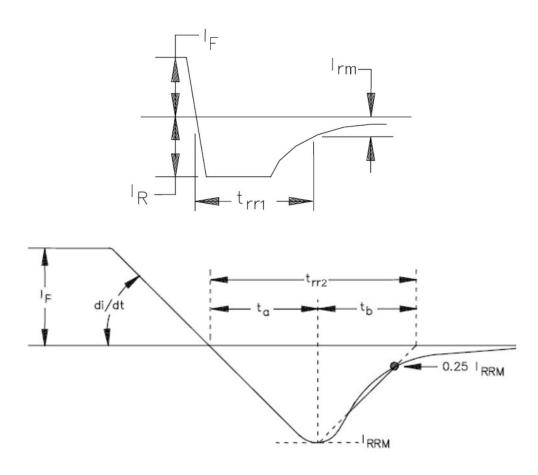
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Note: 1. t_{rr1} MIL-STD-750 Test Method 4031, condition "B". 2. t_{rr2} MIL-STD-750 Test Method 4031, condition "D".

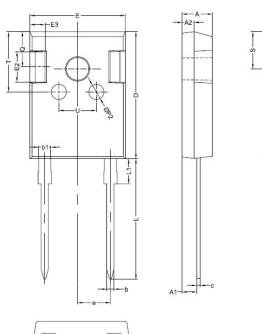
Fig.5-Reverse Recovery Waveform

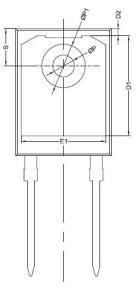






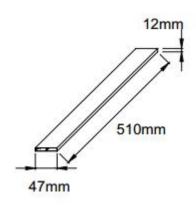
Mechanical Dimensions TO-247AC





CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.35		
b1	1.80	2.00	2.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.58			
D2		1.17			
E	15.60	15.80	16.00		
E1		14.02			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.42		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1	7.19	7.40		
P2		2.50			
		5.80			
Q S T	6.05	6.15	6.25		
Т		10.00			
U		6.20			

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

SDUR = Device Type = Forward Current (60A)

60

120

= Reverse Voltage (1200V) W = Configuration

SSG = SSG = Year WW = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping	
SDUR60H120W	TO-247AC(Pb-Free)	25pcs / tube	

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SDUR60H120W



Technical Data Data Sheet N2576, Rev.-





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